



Corporate Fact Sheet

Fast facts

Founded : August 1999
Employees : 150
Headquarter : Suwon, Korea
Factory size : 64,050 ft²
USA R&D office in Cary, NC.

Management Team

CEO : Mr. David CHO
Founder/CTO:
Dr. Samuel CHO
CFO : Mr. J.Y. LEE
CSO : Mr. I. S. MIN

Contact information

RFHIC Corporation
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Company Profile

RFHIC is a fast growing pioneer in the global wired and wireless market, providing comprehensive product portfolios in the field of active RF components for the infrastructure and broadcasting industry.

RFHIC was founded in 1999, and has been pioneering in the telecommunication and CATV component markets with new technology or new product features ever since. Major area of business include Base Station, Repeaters, Cable Networks, LTE, WiMAX, UMTS, DTV, Radar, Medical, Military, and Test Equipments for infrastructure markets.



As a No.1 active component manufacturer in Korea and expanding customer support across the world, RFHIC is already serving component communication equipments in over 45 international countries, and over 1000 customers.

With ISO9001 certified manufacturing and production facilities, providing reliable & dependable solution is always a key to RFHIC. Being a 'One-stop facility' solution provider, RFHIC is capable of processing MMIC, Die Attach, Wire Bonding, Packaging, Chip on Board, hybrid, SMT Line, RF Test Line, and Quality Control actions all in our facility. This provides customers with very fast delivery, high quality control, high reliability, cost cutting technology, and fast support on engineering sample designs.

Key Product Areas.

- + MMIC & Package IC
- + Hybrid LNA
- + CATV Hybrid Line Amplifier
- + Wideband Amplifier
- + Hybrid Up/Down Mixer, Converter, PLL, Band Switch Filters & Other Components
- + Integrated Modules and Sub-Systems
- + GaN/GaAs Hybrid PA, Pallet PA, Connectorized Power Amplifiers
- + Repeater/CPE For WiMAX, 3G(UMTS, WCDMA)

Core Competencies

- + Price Leadership : Key to stay competitive and grow, keeping cost advantages inline with quality goals are the biggest challenge we are constantly winning.
- + Simulation & Design : Forward thinking product development to satisfy future customer demand
- Package & Hybrid Technology : High integration is possible by utilizing chip-on-board (COB) technology to build multi-chip modules(MCM).
- + Multiple Foundry Service : 6 different foundry service to maximize different technology advantages according to needed specifications.
GaAs HBT/ GaAs P-HEMT/ GaAs MESFET/ GaAs E-PHEMT/ GaN HEMT / Silicon MEMS
- + Broad Wireless Component base : Total solution for a wide selection of components encompassing all active components in the RF transceiver design.
- + One Stop Process : Fast & reliable time to market manufacturing with high quality control and low cost
- + Integrated Sub-Module Experience : Experienced complex module/sub-system designs which will help support custom designs. Small form factor, hybrid design specialists.

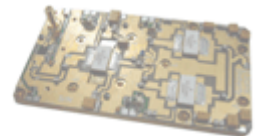
GaN Specialization

Gallium nitride, or GaN, is touted as the last frontier in semiconductor technology. GaN is a member of the wide-bandgap family of semiconductors, and hold the most promise in semiconductor applications that demand high power and/or high bandwidth handling capabilities. These capabilities will become increasingly important as today's silicon- and gallium arsenide-based semiconductors have reached their limit just as power- and bandwidth-intensive applications (e.g. : third-generation, or 3G, communications) are set to take off.

GaN's physical nature includes;

- High thermal conductivity
- High melting temperature
- Low dielectric constant
- High breakdown voltage

which translate to fundamental performance advances in the area of high power, high frequency power transistors for RF transmission applications covering the 1-50 GHz band.



Applications for GaN includes mobile communications; wireless local, metropolitan and wide area networking; point-to-point (LMDS) and point-to-multipoint (MMDS) microwave communications; and radar applications, GaN holds the promise of redefining the feasibility, cost and capabilities of the full range of radio communications technologies and systems.

RFHIC GaN devices and power amplifiers, which use GaN-on-Si & GaN-on-SiC technology as a building block, are now available for large-scale production with proven reliability.